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Katsunori ASANO et al.

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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

						TRANSLATION	
	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO
	2003-31802	1/2003	Japan			ABSTRACT	
	2001-291869	10/2001	Japan			ABSTRACT	
	2002-231947	08/2002	Japan			ABSTRACT	
	10-284733	10/1998	Japan			ABSTRACT	
	10-256529	09/1998	Japan			ABSTRACT	
	10-27899	01/1998	Japan			ABSTRACT	

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

International Search Report of PCT/JP2005/004834 mailed 28 June 2005
Ryu et al., "High-Power P-Channel UMOS IGBT'S in 6H-SiC for High Temperature Operation", Materials Science Forum, Vols. 338-342, pp. 1427-1430 (2000)

*Examiner

/Paul Patton/

Date Considered

07/17/2009

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include count of this form if next communication is a reply.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /P.P./